

SuperMOS – PDFN3X3-8L 30V V_{DSS} 4m Ω $R_{DS(on)}$, N-channel MOSFET

1. Description

The WSD3066DN33-ES is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product WSD3066DN33-ES is Pb-free.

2. Features

- 30V, $R_{DS(ON)}=4.0m\Omega(TYP.) @V_{GS}=10V$
 $R_{DS(ON)}=6.5m\Omega(TYP.) @V_{GS}=4.5V$
- Use trench MOSFET technology
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications


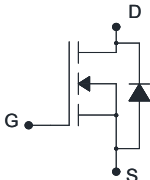
- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

100% UIS TESTED!

4. Ordering Information

Part Number	Package	Marking	Material	Packin g	Quantit y per reel	Flammabilit y Rating	Reel Size
WSD3066DN33-E S	PDFN3X3-8 L	ES3343/LO T	Haloge n free	Tape & Reel	5,000 PCS	UL 94V-0	13 inche s

5. Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
4	Gate		
1/2/3	Source		
5/6/7/8	Drain		

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	$T_C=25^{\circ}C$	I_D	45	A
	$T_C=75^{\circ}C$		35	
Maximum Power Dissipation	$T_C=25^{\circ}C$	P_D	30	W
	$T_C=75^{\circ}C$		18	
Pulsed Drain Current ^a		I_{DM}	180	A
Avalanche Current, Single Pulsed ^b		I_{AS}	30	A
Avalanche Energy, Single Pulsed ^b		E_{AS}	135	mJ
Operating Junction Temperature		T_J	150	°C
Lead Temperature		T_L	260	°C
Storage Temperature Range		T_{stg}	-55 to 150	°C

Thermal resistance ratings

Single Operation				
Parameter		Symbol	Typical	Unit
Junction-to-Ambient Thermal Resistance	$t \leq 10\text{ s}$	$R_{\theta JA}$	40	°C/W
Junction-to-Case Thermal Resistance	Steady State	$R_{\theta JC}$	4.2	

Note:

a: Repetitive rating, pulse width limited by junction temperature, $t_p=10\mu\text{s}$, Duty Cycle=1%

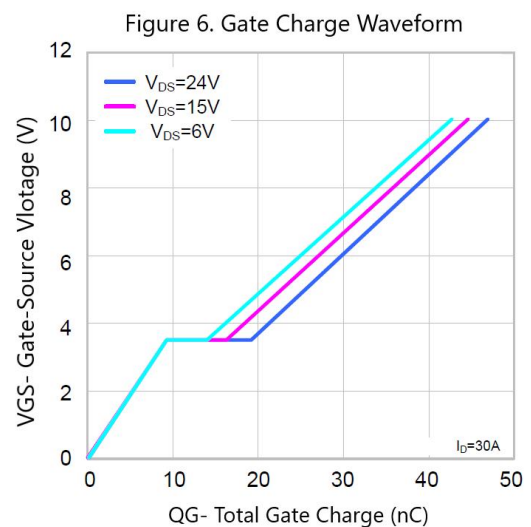
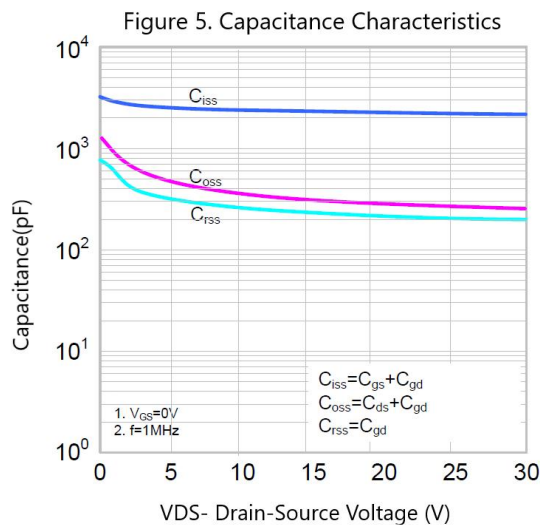
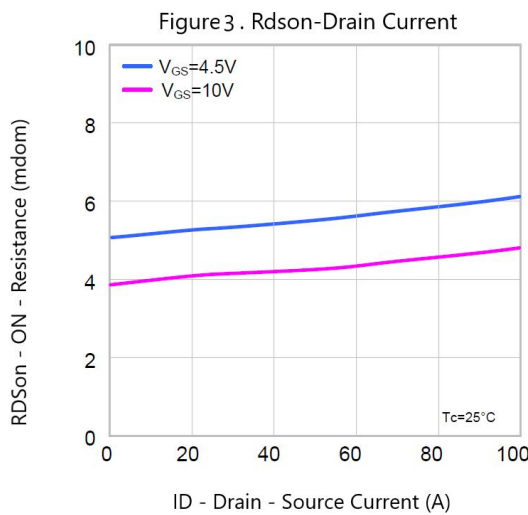
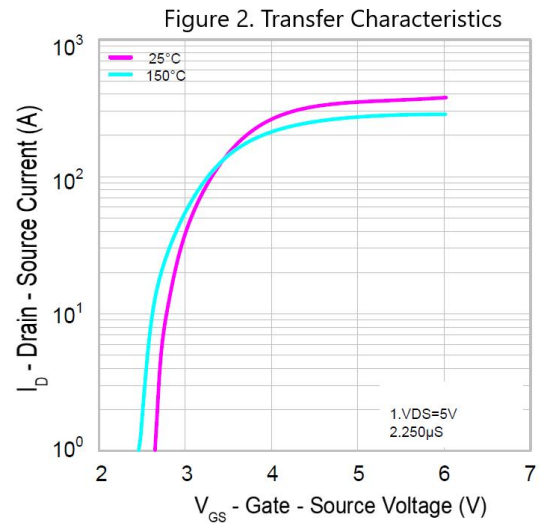
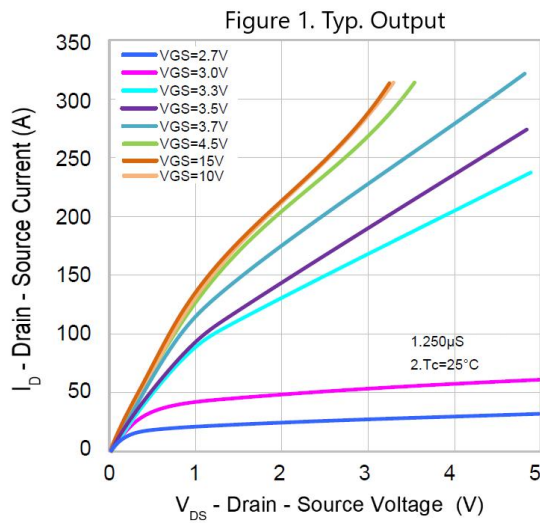
b: EAS condition: $T_J=25^{\circ}C, V_{DD}=30V, V_G=10V, L=0.3mH, R_g=25\Omega$

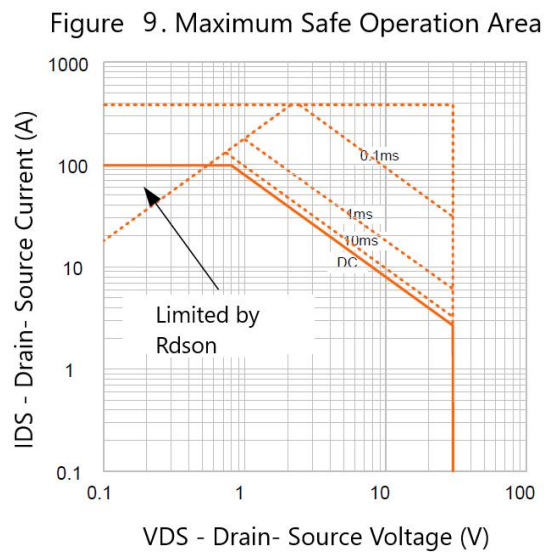
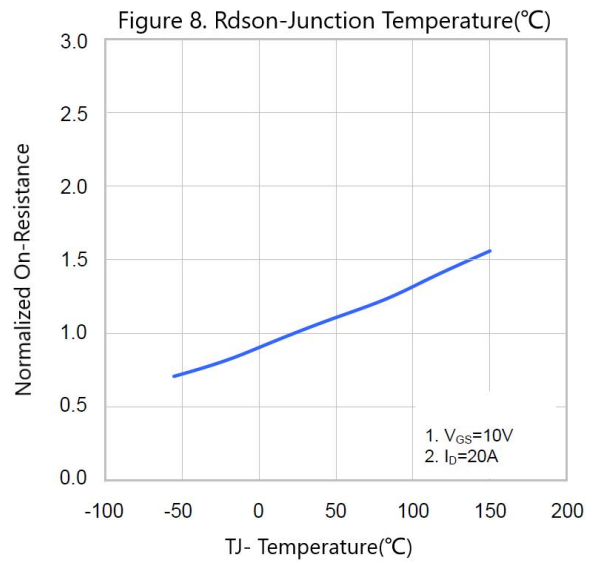
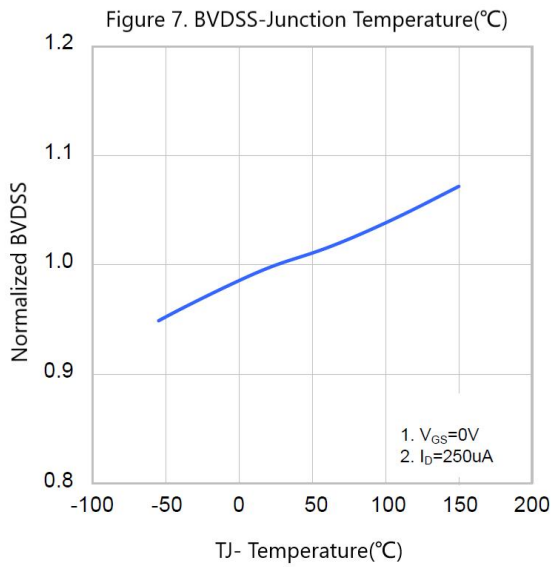
Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1.0	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.75	2.5	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		4.0	7.5	m Ω
		$V_{GS}=4.5V, I_D=16A$		6.5	9.5	
Forward Trans conductance	g_{FS}	$V_{DS}=5.0V, I_D=10A$		25	40	S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS}=0V, f=1MHz, V_{DS}=25V$		2200		pF
Output Capacitance	C_{OSS}			275		
Reverse Transfer Capacitance	C_{RSS}			242		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=10V, V_{DS}=24V, I_D=30A$		48		nC
Gate-to-Source Charge	Q_{GS}			8.8		
Gate-to-Drain Charge	Q_{GD}			10.0		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=4.5V, V_{DS}=20V, I_D=60A, R_G=1.8\Omega$		12.5		ns
Rise Time	t_r			90		
Turn-Off Delay Time	$t_{d(OFF)}$			142		
Fall Time	t_f			85		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=1.0A$		0.75	1.5	V

7. Typical Characteristic





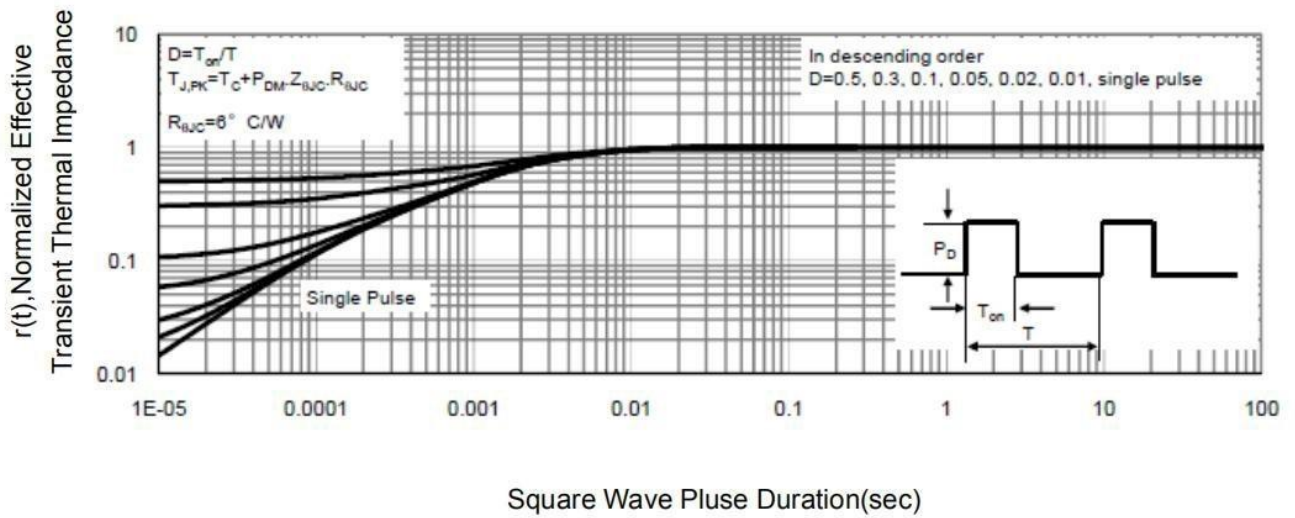
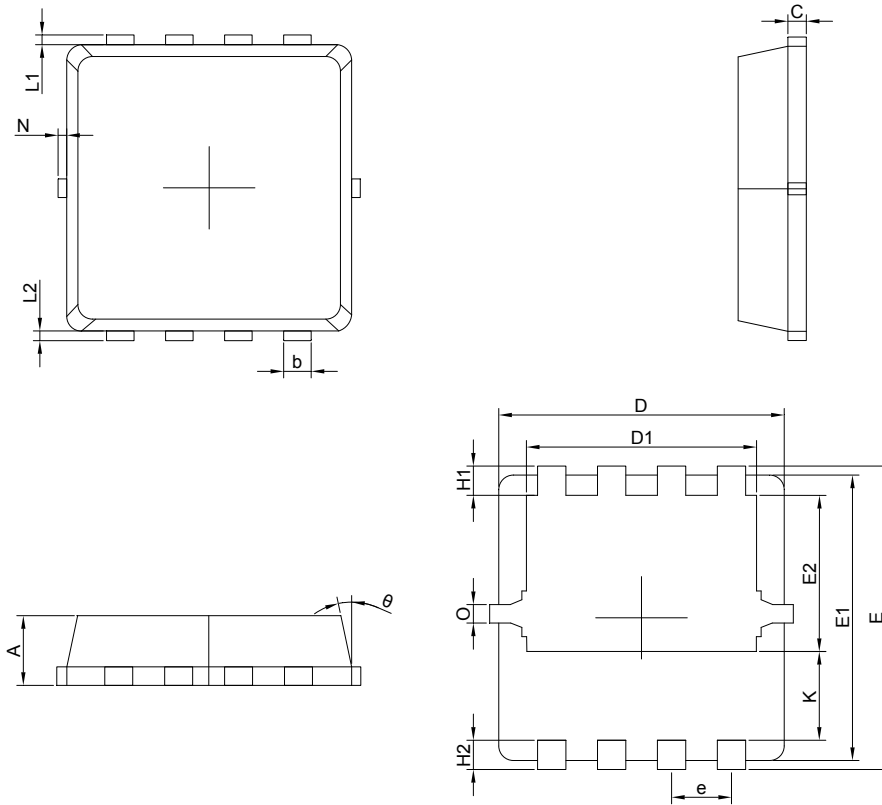


Figure 10 Normalized Maximum Transient Thermal Impedance

8. Dimension (PDFN3X3-8L)



Symbol	Dimensions in Millimeters			Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX		MIN	NOM	MAX
A	0.65	0.75	0.85	e	0.65 BSC.		
b	0.25	0.30	0.35	H1	0.21	0.31	0.41
C	0.15	0.20	0.25	H2	0.30	0.40	0.50
D	3.00	3.10	3.20	K	0.78	0.88	0.98
D1	2.40	2.50	2.60	L1/L2	0.10 REF.		
E	3.20	3.30	3.40	θ	11°	12°	13°
E1	3.00	3.10	3.20	N	0	-	0.15
E2	1.60	1.70	1.80	O	0.2 REF.		

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